

GT50JR22

1. Applications

- Dedicated to Current-Resonant Inverter Switching Applications

Note: The product(s) described herein should not be used for any other application.

2. Features

- (1) 6.5th generation
- (2) The RC-IGBT consists of a Freewheeling Diode(FWD) monolithically integrated in an IGBT chip.
- (3) Enhancement mode
- (4) High-speed switching
IGBT : $t_f = 0.05 \mu s$ (typ.) ($I_C = 50 A$)
FWD : $t_{rr} = 0.35 \mu s$ (typ.) ($I_F = 15 A$)
- (5) Low saturation voltage : $V_{CE(sat)} = 1.55 V$ (typ.) ($I_C = 50 A$)
- (6) High junction temperature : $T_j = 175^\circ C$ (max)

3. Packaging and Internal Circuit

